

Flyback transformer

more
than you
expect



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WE Group: transformer players

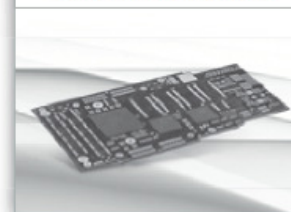


The Würth Elektronik Group

Electronic & Electromechanical Components



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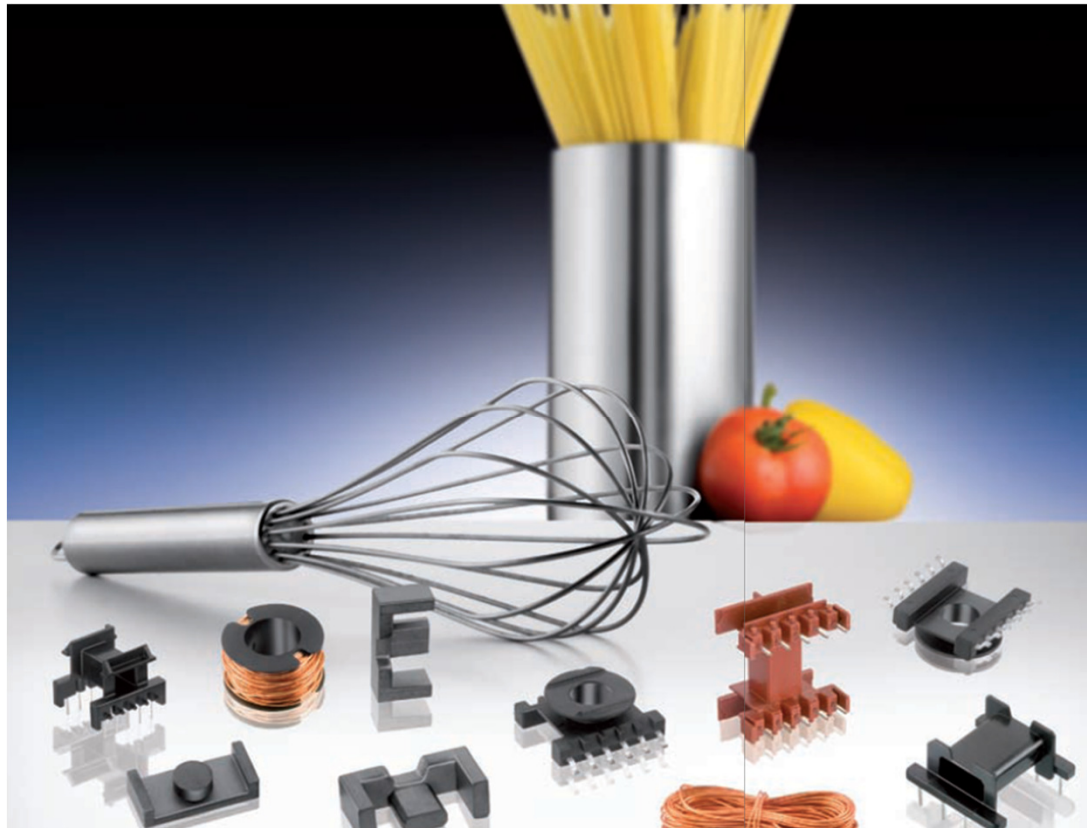
Automotive



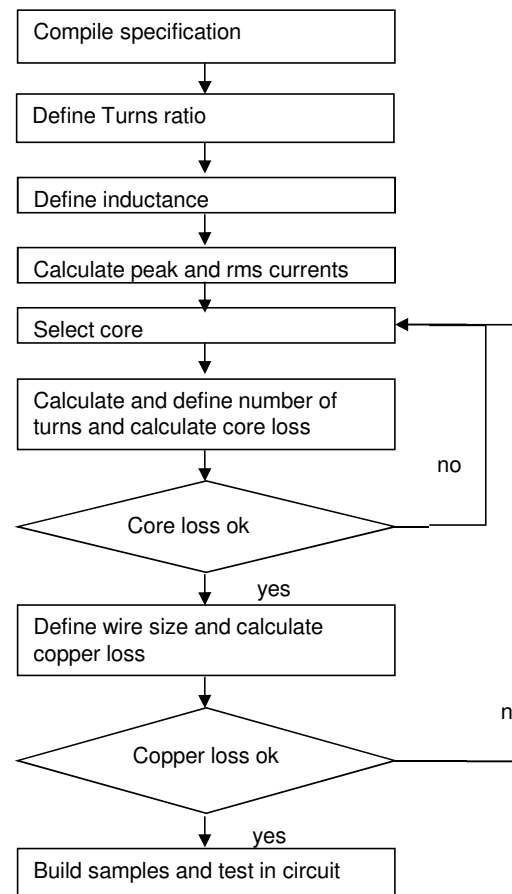
Magnetics



Transformer Design: General sequence



Design of a Custom Flyback transformer



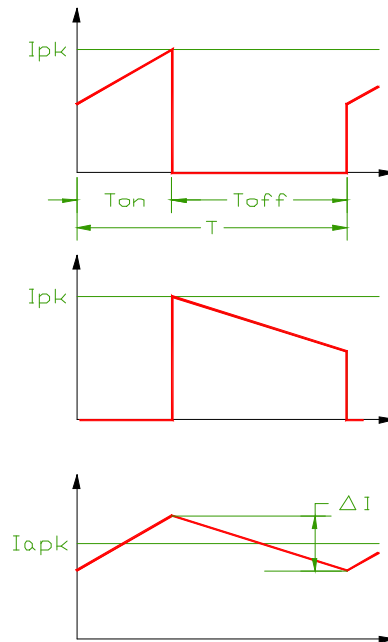
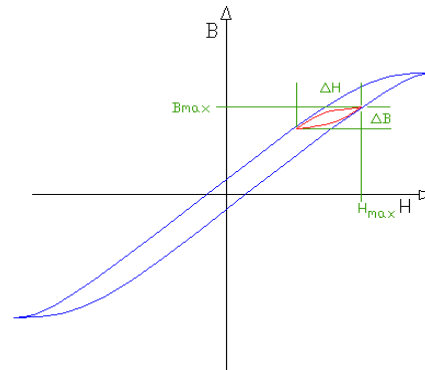


Basic Principles

The Flyback Converter



- CCM
 - The primary current never drops to zero during all operating conditions
 - Primary Inductance value is relatively bigger.
 - Two states per switching cycle:
 - The ON state: Transistor is ON and Diode is OFF
 - The OFF state: Transistor is OFF and Diode is ON
 - Lower ripple currents
 - Right hand plane zero
 - Core losses are lower
 - Flux swing is smaller
 - Improved EMC properties
 - Worst case at low V_{in}

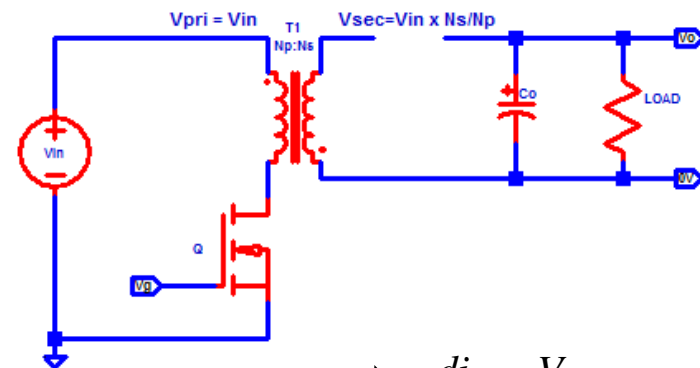
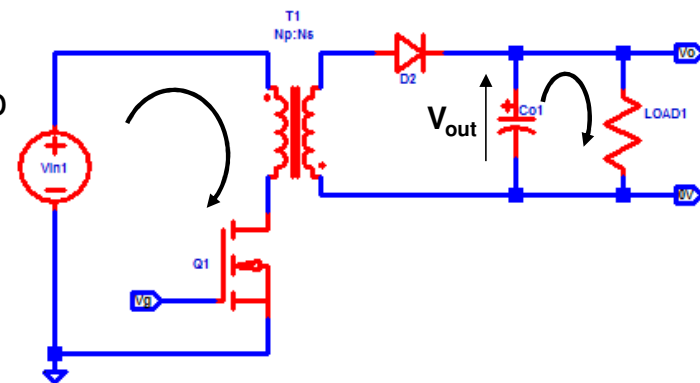
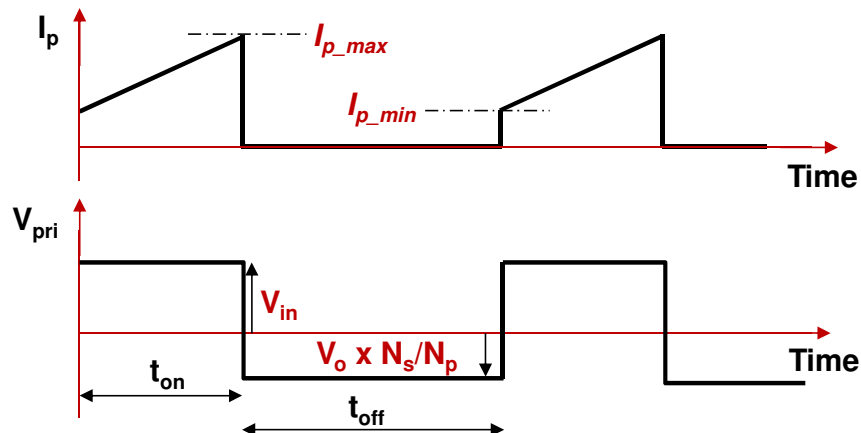


The Flyback Converter (CCM)

- Switch closed (Transistor ON):
 - Primary winding current rises from I_{p_min} to I_{p_max} in $t_{on} = DT$

$$\Delta I_p = \frac{V_{in} \times DT}{L_p}$$

$$I_{p_max} = \frac{V_{out} \times I_{out}}{\eta \times D \times V_{in}} + \frac{\Delta I_p}{2}$$



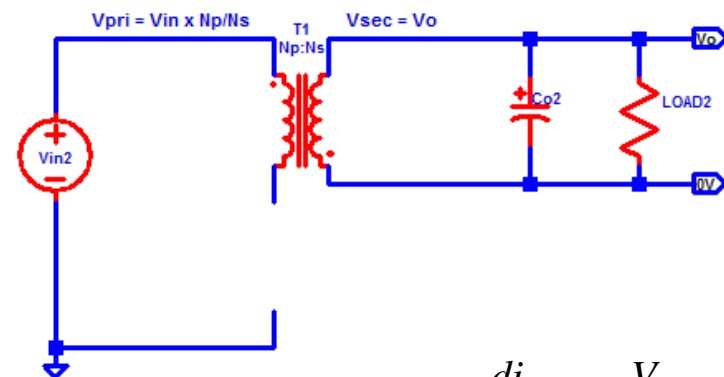
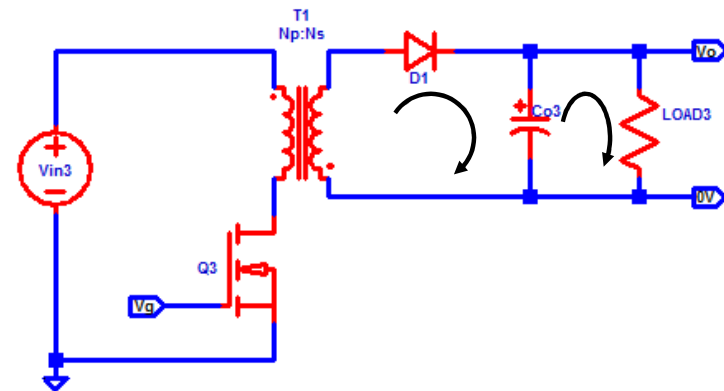
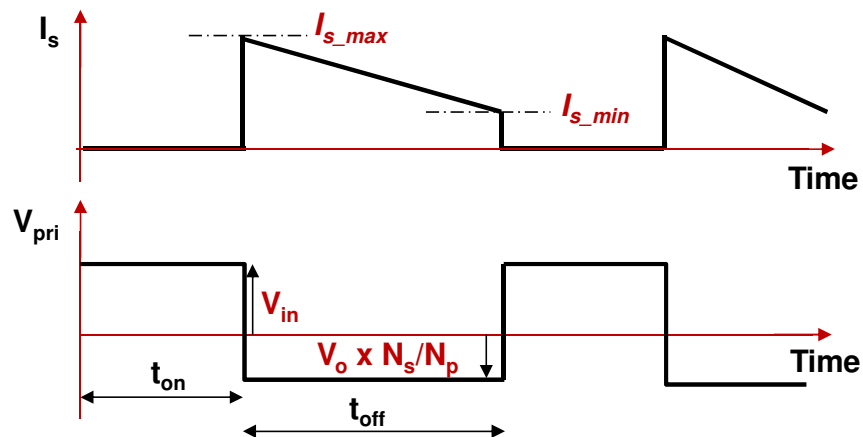
$$V_{Lp} = V_{in} \Rightarrow \frac{di_L}{dt} = \frac{V_{in}}{L_p}$$

The Flyback Converter (CCM)

Switch opened (Transistor OFF):

- Secondary winding current falls from I_{s_max} to I_{s_min} in $t_{off} = (1-D)T$.

$$\Delta I_s = \Delta I_p \times \frac{N_p}{N_s} \quad I_{s_max} = I_{p_max} \times \frac{N_p}{N_s}$$



$$V_{Ls} = -V_{out} \Rightarrow \frac{di_{Ls}}{dt} = \frac{-V_{out}}{Ls}$$

The Flyback Converter (CCM)

- **Critical inductance value ($L_{critical}$):**
 - At Boundary of CCM/DCM
 - Minimum inductance to obtain a continuous conduction mode at minimum output power

$$L_{Critical} > \frac{V_{out}^2}{2P_{out_min} \cdot f_{switch}} \times \frac{1}{\left(\frac{N_s}{N_p} + \frac{V_{out}}{V_{in_max}} \right)^2}$$

- **Turns Ratio:**

$$\frac{N_s}{N_p} = \frac{V_{out}}{\sqrt{V_{in_min} \times V_{in_max}}}$$

The Flyback Converter (CCM)

- CCM Design Equations:

$$VCR = \frac{V_{out}}{V_{in}} = N \times \frac{D}{1-D} \quad ; \quad \text{where: } N = \frac{N_s}{N_p} \quad \text{VCR = Voltage Conversion Ratio}$$

$$\Delta I_p = \frac{V_{in} \times DT}{L_p}$$

$$V_D = V_{out} + (V_{in} \times \frac{N_s}{N_p})$$

$$V_T = V_{in} + (V_{out} \times \frac{N_p}{N_s})$$

$$I_{p_max} = \frac{V_{out} \times I_{out}}{\eta \times D \times V_{in}} + \frac{\Delta I_p}{2}$$

$$L_p = \frac{V_{out}^2}{2 P_{out} \cdot f_{switch}} \times \frac{1}{\left(\frac{N_s}{N_p} + \frac{V_{out}}{V_{in_max}} \right)^2}$$

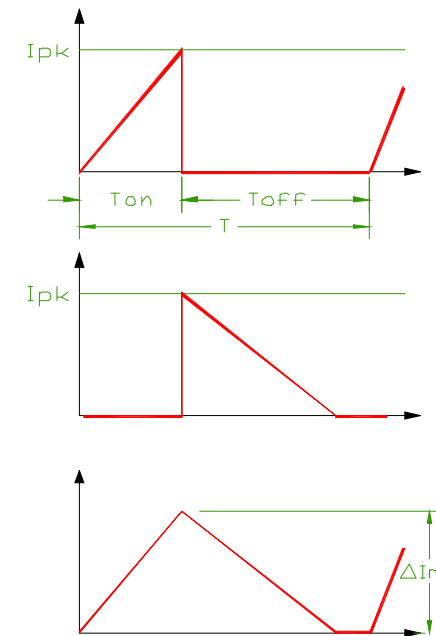
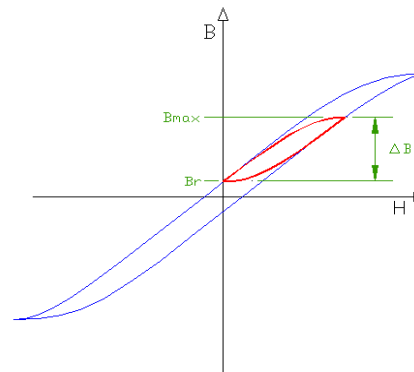
$$I_{in} = \frac{V_{out} \times I_{out}}{\eta \times V_{in}} = \frac{N \times D \times I_{out}}{(1-D) \times \eta}$$

The Flyback Converter



■ DCM

- The primary current drops to zero.
- Primary Inductance value is relatively smaller. Capacitance may need to be larger.
- Three states per switching cycle:
 - The ON state: Transistor is ON and Diode is OFF
 - The OFF state: Transistor is OFF and Diode is ON
 - The IDLE state: Both Transistor and Diode are OFF
- MOSFET turn on at zero current
- Worst case at low V_{in}

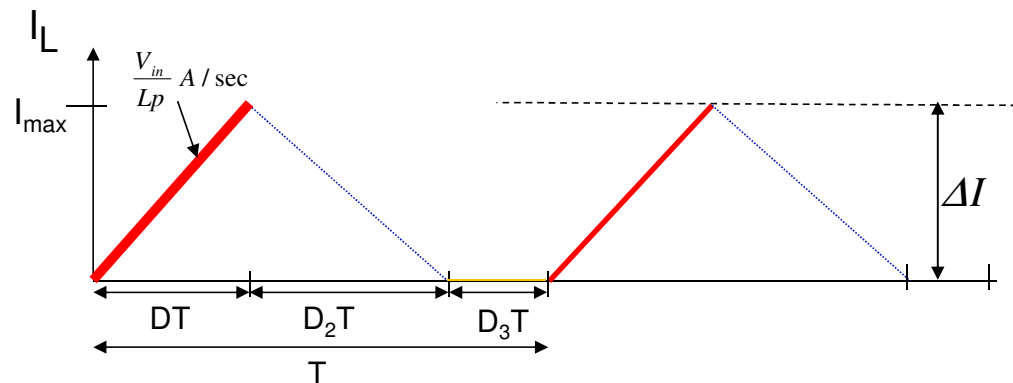
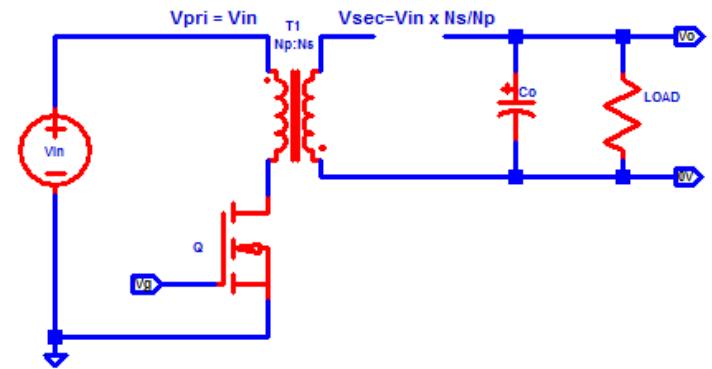


The Flyback Converter (DCM)

- Switch closed (Transistor ON):
 - Primary winding current rises from zero to I_{p_max} in $t_{on} = DT$

$$I_{p_max} = \Delta I_p = \frac{V_{in} \times DT}{L_p}$$

$$D = \frac{\sqrt{2 \times P_{in} \times L_p \times f}}{V_{in}}$$



The Flyback Converter (DCM)

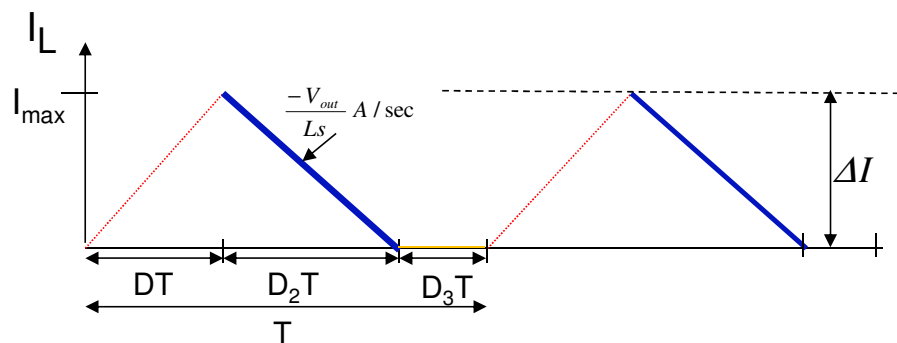
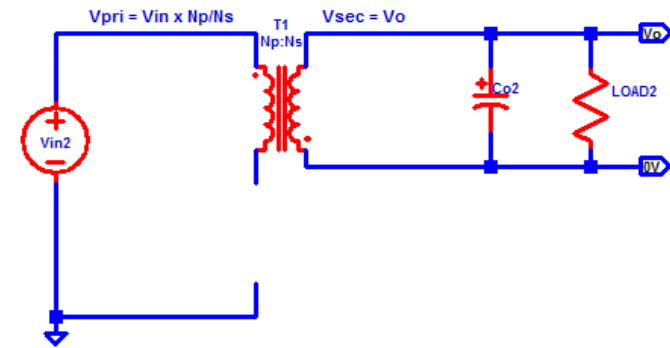
Switch opened (Transistor OFF):

- Secondary winding current falls from I_{s_max} to zero in $t_{off} = D_2 T$.

$$I_{s_max} = I_{p_max} \times \frac{N_p}{N_s}$$

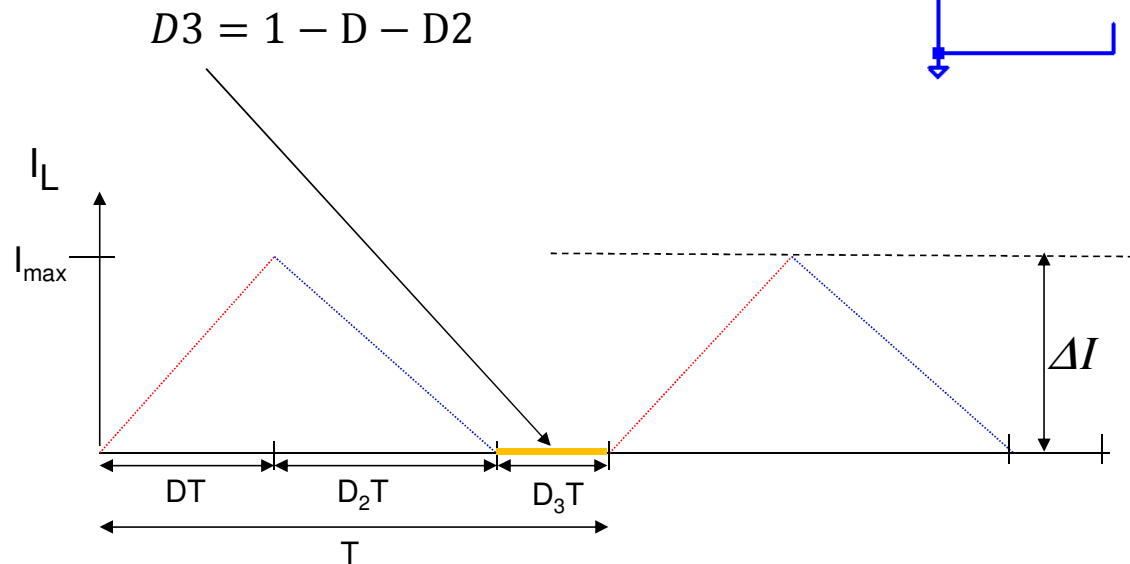
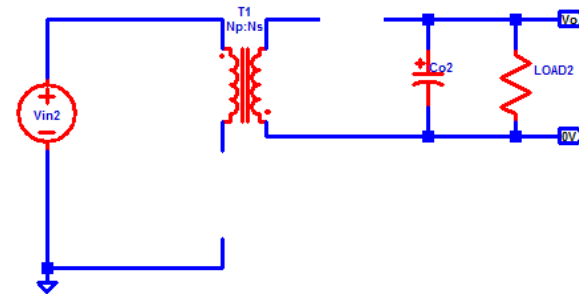
$$D_2 = \frac{\sqrt{2 \times P_{out} \times N^2 \times L_p \times f}}{V_{out}}$$

$$N = \frac{N_s}{N_p}$$



The Flyback Converter (DCM)

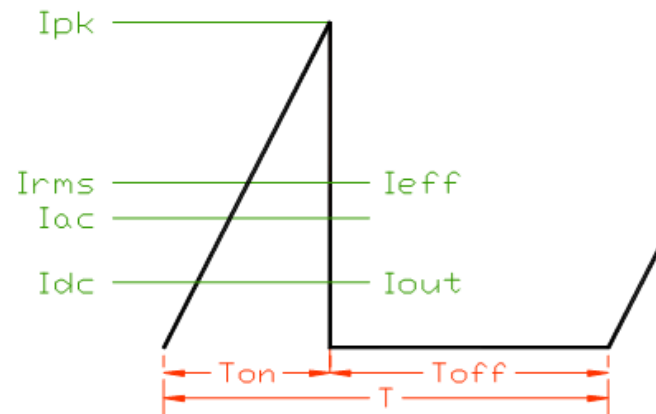
- **Idle State (Transistor & Diode OFF):**
 - Only Capacitor delivers energy to load during D_3T



The Flyback Converter (DCM)

- Inductance value (L_{DCM}):
 - Maximum inductance to obtain a discontinuous conduction mode at maximum output power

$$L_{DCM} < \frac{V_{out}^2}{2P_{out_max} \cdot f_{switch}} \times \frac{1}{\left(\frac{N_s}{N_p} + \frac{V_{out}}{V_{in_min}} \right)^2}$$



Comparison Discontinuous / Continuous Flyback

Continuous Flyback	Discontinuous Flyback
Still current on diode when „switching“ off => needs a ultrafast switching diode	Current on diode already Zero when „switching“ off
No ringing on MOSFET	Ringing at MOSFET when current becomes Zero
Duty cycle is well defined	Duty cycle is not defined because of dead time
Peak currents are variable	Fixed peak current
	Secondary triangle is fix
Low peak current	High peak current
Low ripple current	High ripple current
High inductance	Low inductance

Pick a Core – AreaProduct – AP Product

Making the conversion of current density from A/m² to cmils/A and units into CGS for convenience we get

$$AP = \frac{506.7 \cdot P_{in} \cdot J_{cmils/A}}{K \cdot f \cdot \Delta B} \text{ cm}^4$$

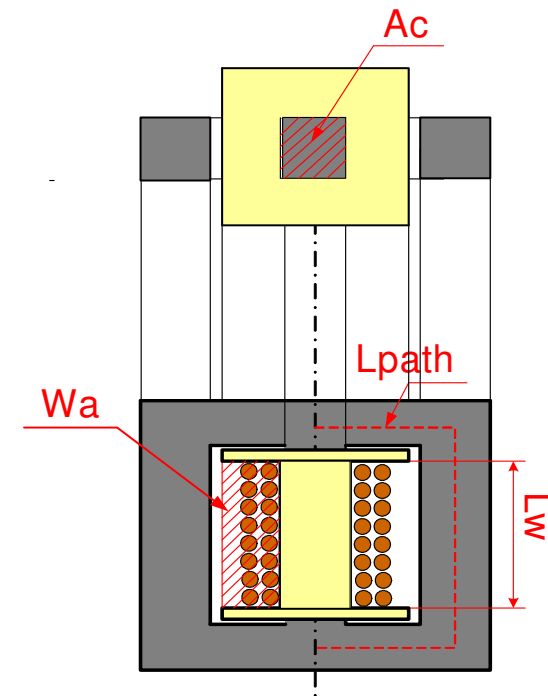
$$AP = WaAc$$

Typical value for K is 0.3-0.4 and for $J_{cmils/A}$ is 300-600

AP EFD15= 0,019

AP EF16= 0,043

AP EFD20= 0,087



Wa = Window Area in cm²

Ac = Core Area in cm²

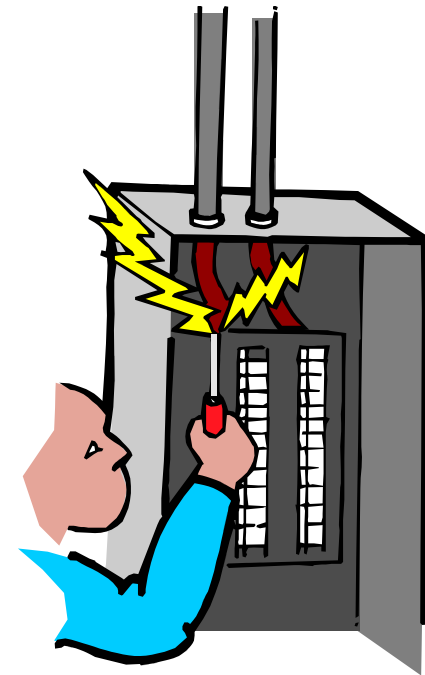


Safety requirements

Safety requirements



- **standards:**
e.g. EN (IEC)60950, (IT-equipment)
EN (IEC)61558 Part 2-16 (transformer general)
- **standards define**
 - Clearance distance
 - Creepage distance
(depends on pollution degree)
 - Distance through insulation
- **standards define**
 - electrical breakdown voltage
- **There are differences between the standards!**



Safety requirements



- Defining the Insulation Level requires:
 - Grade of Insulation (Functional, Basic, Supplementary, Reinforced)
 - Working Voltage
 - Pollution Degree
- This information is application dependent.
- It is not driven by the transformer.
- It's impact on the transformer construction & price can be significant.

Safety requirements



- **Working Voltage**

- Highest voltage to which the insulation or the component under consideration is, or can be, subjected to when the equipment is operating under conditions of normal use.

- **Pollution Degrees**

- Degree 1 – Assemblies which are sealed so as to exclude dust and moisture.
- Degree 2 - Office and laboratory areas are considered pollution degree 2 environments
- Degree 3 - Conductive pollution or dry nonconductive pollution that becomes conductive when condensation occurs. To be found in industrial environment or construction sites.

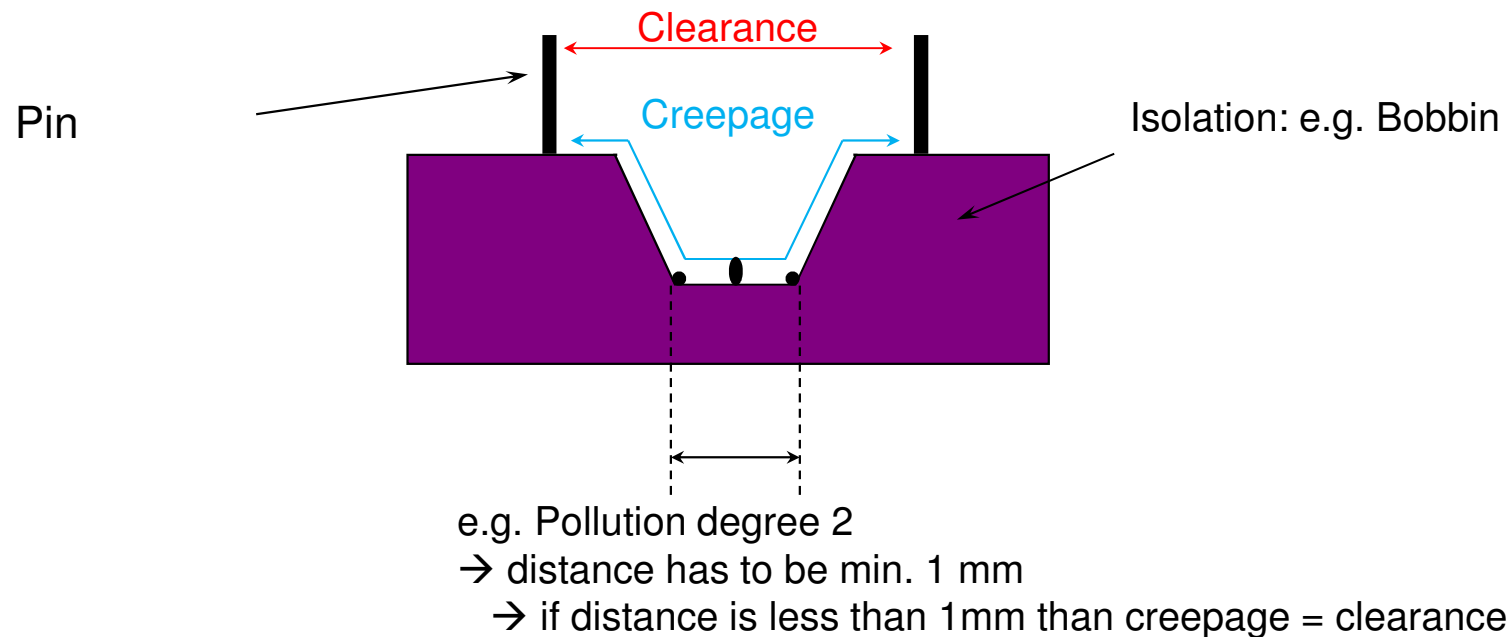
- **Creepage Distance**

- Shortest distance through air along the surface of an insulation material between two conductive parts

- **Clearance Distance**

- Shortest distance in air between two conductive parts

Clearance and creepage distance



- **Clearance**
→ distance in air (conductor to conductor)
- **Creepage**
→ distance along surface (conductor to conductor)

Isolation test voltage

- Isolation test voltages according to EN61558

Operating voltage [V _{RMS}]	Isolation test voltage [V _{RMS}]	
	Basic insulation	Reinforced insulation
50	250	500
150	1400	2800
300	2100	4200
400	2200	4500
1000	2750	5500

→ It is not enough to mention ONLY a test voltage as safety requirement

Safety requirements

- Creepage distances for different working voltages

Example: Pollution degree 2 according to IEC61558-2-16

Working voltage (RMS)	Creepage distance pollution degree 2 [mm]					
	Basic insulation			Reinforced insulation		
	CTI>600	400<CTI<600	CTI<400	CTI>600	400<CTI<600	CTI<400
100	0,8	1,1	1,5	1,1	1,5	2,2
150	0,9	1,2	1,8	1,7	2,2	3,3
300	1,7	2,3	3,3	3,3	4,7	6,6
400	2,2	3,1	4,4	4,4	6,4	8,8
600	3,3	4,7	6,6	6,6	9,5	13,2
1000	6,1	2,4	11,0	11,0	15,4	22,0

→ the creepage distance cannot be less than clearance distance

Safety requirements

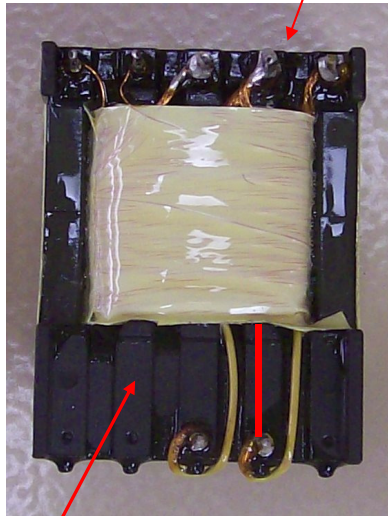
- **Comparative Tracking Index (CTI)**

- CTI of raw material effects the creepage distance
- CTI value is a measure of the resistance to surface tracking that a particular material exhibits under specific test conditions
- the smaller the CTI for that material, the bigger the creepage distance required

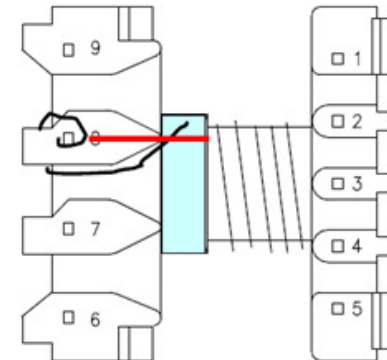
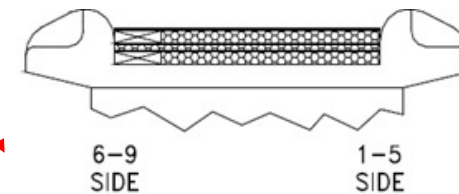


How to Achieve Creepage Distances

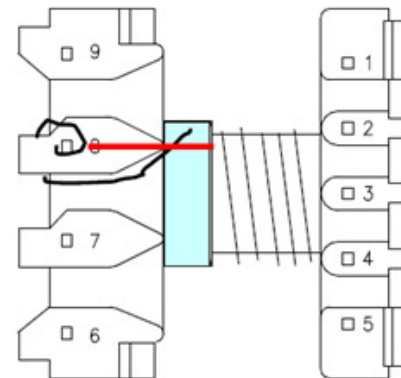
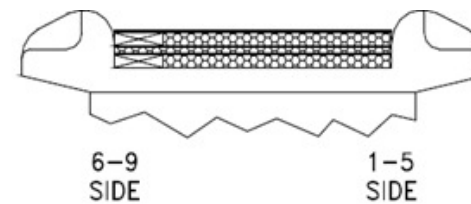
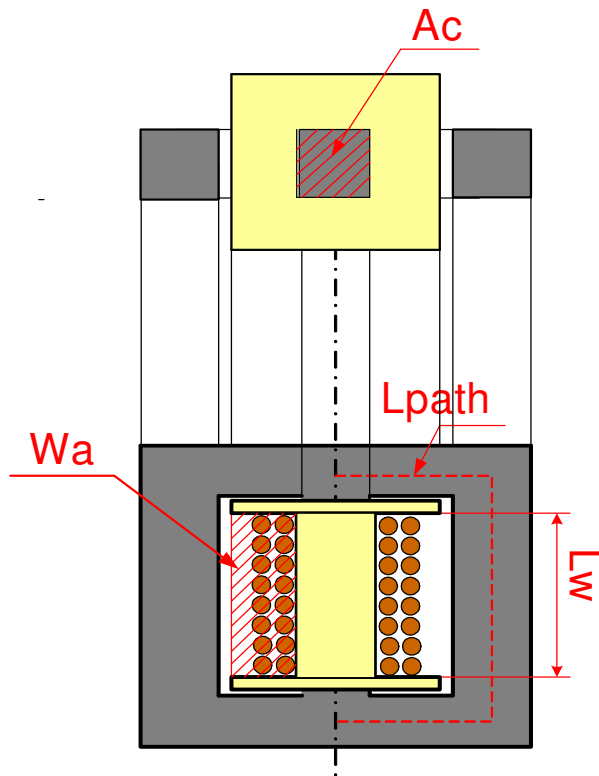
- Use extended rail bobbin and / or margin tape to increase distance from SEC pins to PRI winding



Triple Insulated Wire on SEC to insulate windings



AP product Vs Creepage- Warning



WE-UOST example

It is recommended that the temperature of the component does not exceed +125°C under worst case conditions

Storage Temperature (in original packaging)

-20 °C up to +60 °C

Operating Temperature

-40 °C up to +125 °C

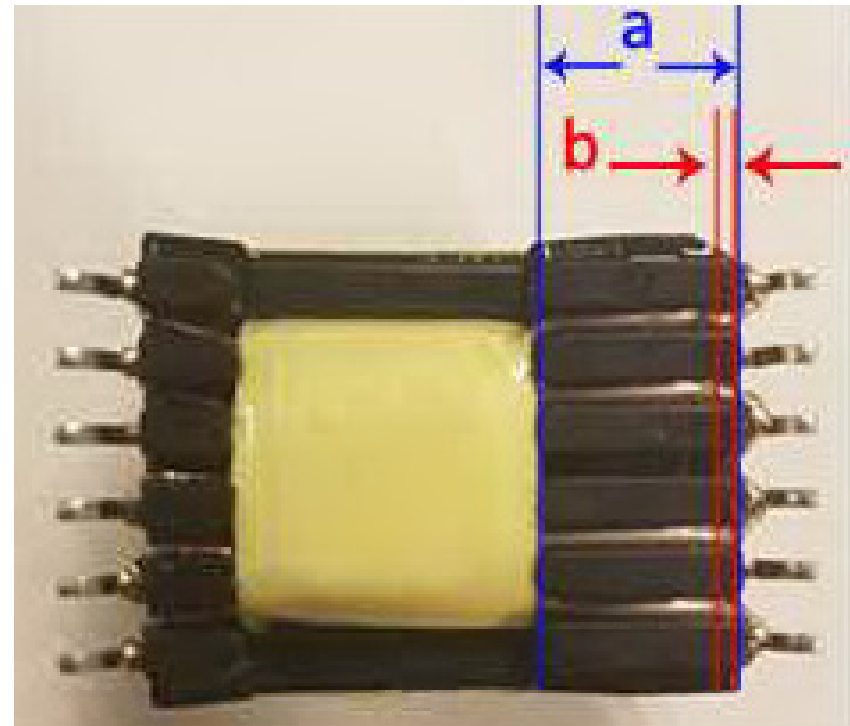
Test conditions of Electrical Properties: +20°C, 33% RH if not specified differently

Designed to comply with the following requirements as defined by IEC61558-2-16; Reinforced insulation for a working voltage of 375 V_{RMS}

a : 7,14 mm min

b : 0,5 mm allowed of wires burnt back

=> Creepage distance minimum 6,6 mm





Manufacturing

Why do we do design for Manufacturing?



- **To increase reliability**
 - Adapt the design to use proven and repeatable processes

- **To reduce cost**
 - Use automated processes where possible
 - Reduce scrap

- **To reduce lead time**
 - Higher throughput using standard processes
 - Reduce rework
 - Use standard components

The Transformer Manufacturing Process

Considerations:

- Winding
- Termination
- Soldering

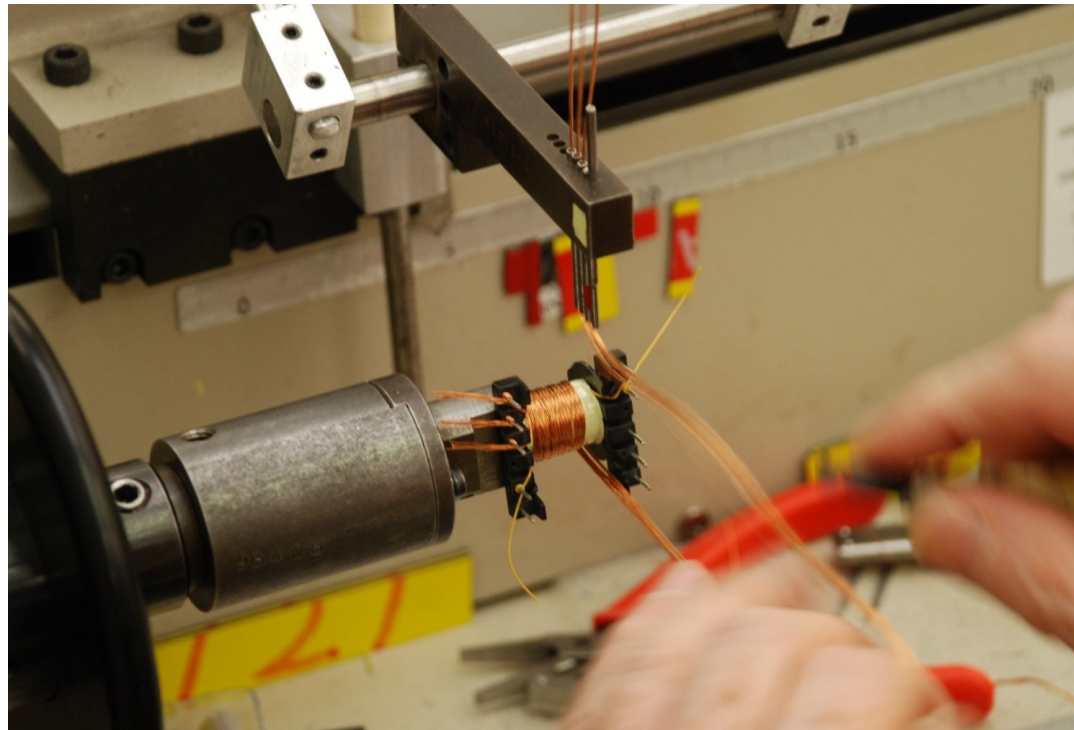


Winding

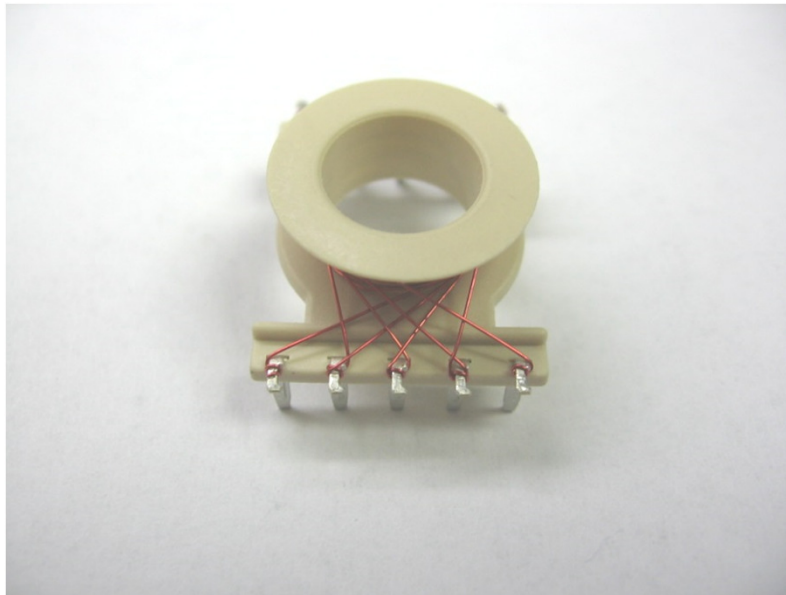


Considerations:

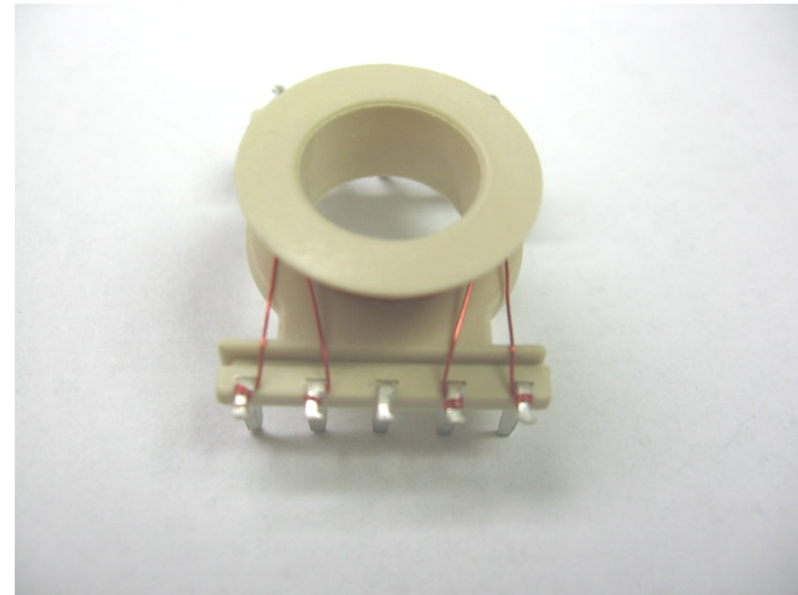
- Pinout
- Layering
- Dragbacks



Pinout – Wires crossing



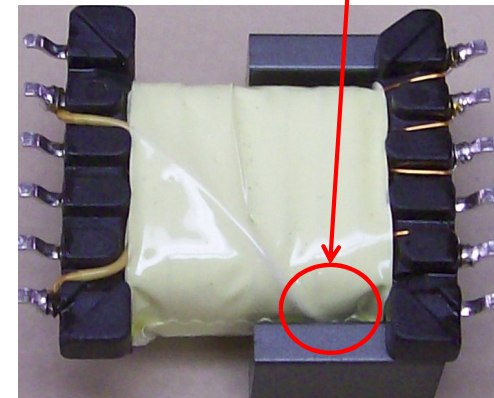
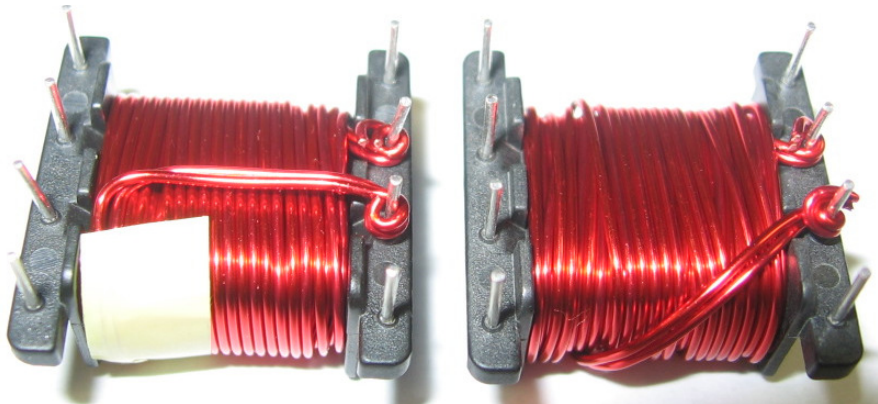
Wire crossings can cause both mechanical and dielectric stress



This is the ideal pin assignment

Wire Dragbacks

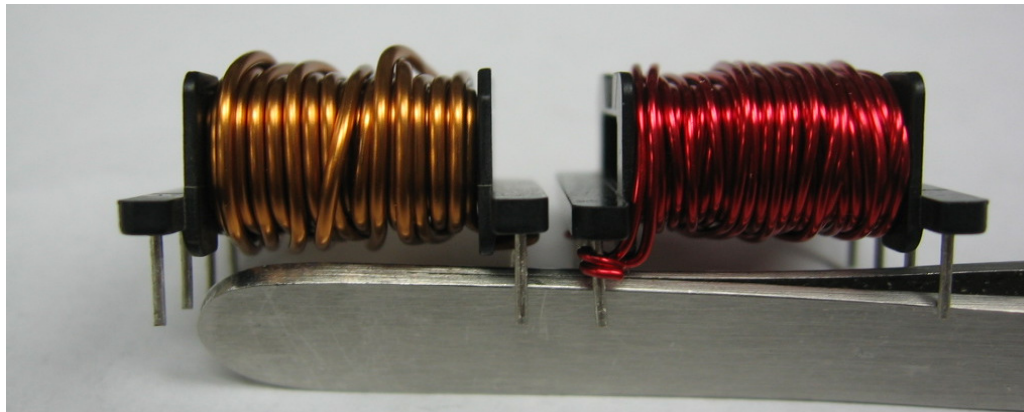
- **Dragbacks can be damaged by winding pressure from subsequent layers**
 - Start tape before dragback (higher labour)
- **90° dragbacks increase labor and may need extra tape**
- **Spiral dragbacks can cause core fit issues**



Layering



- **Adjust wire diameter and number of strands to fill layers**



The coil on the right uses a two-bi winding to achieve the same DC resistance, but better layering.

- **Choose pinout that promotes good layering**
 - Same rail pinout for even number of layers
 - Cross bobbin pinout for odd number of layers

Soldering

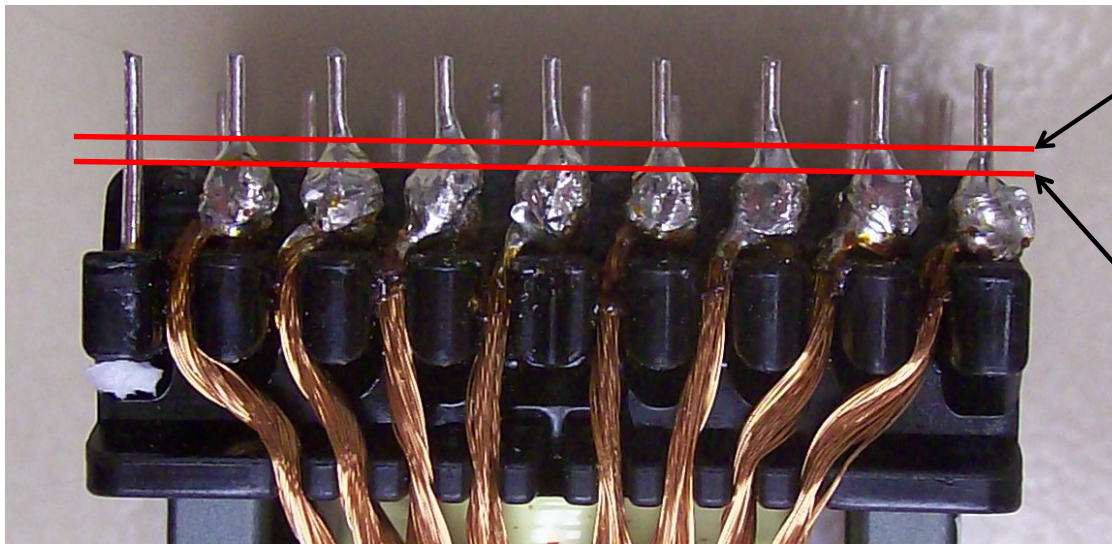


- **A large single strand is more difficult to solder than multiple lighter strands**
 - Large strands: more heat, more time - more insulation damage
- **Avoid using heavy or litz windings on same bobbin rail with fine wire windings**
 - Ideally windings on same bobbin rail should be within 3 gauges
- **Sometimes it makes sense to use heavier wire than necessary for soldering – e.g. matching aux wire size to primary, even if current density doesn't require it (also reduces BOM)**
 - May need two soldering operations if wire mismatch is unavoidable

Solder Terminations



- Large wire terminations on TH parts can cause height issues



Large Wire Wraps –
this is where part will
actually contact PCB

Bobbin Standoff – this
surface should
contact PCB

To Summarize....



Design For Manufacturing:

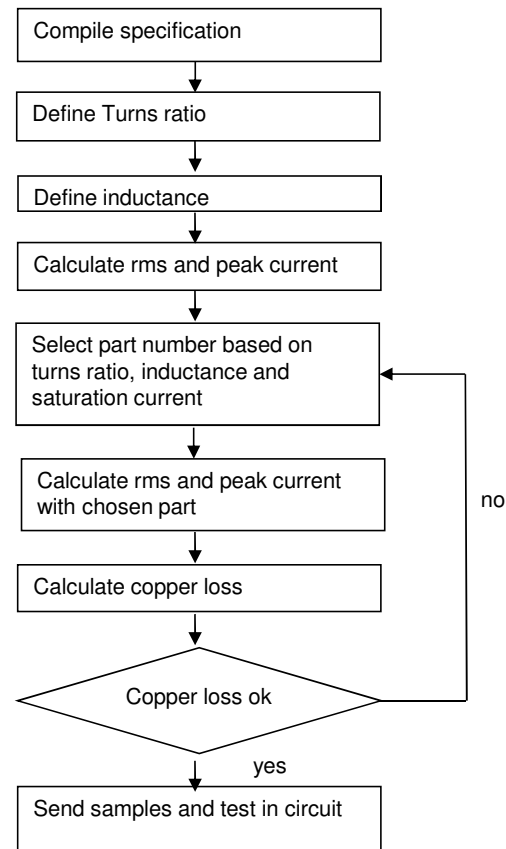
***The practice of considering the manufacturing process
during the design stage***

To increase reliability

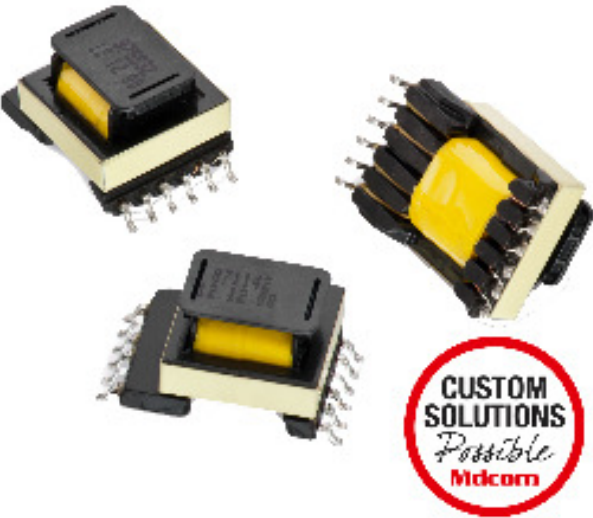
To reduce cost and lead time

Involve us as early as possible in design phase!

Selection of a standard flyback transformer



Example with UOST/UNIT series



Size	L (mm)	W (mm)	H (mm)
EE16/8/5	25.81	16.6	13.5

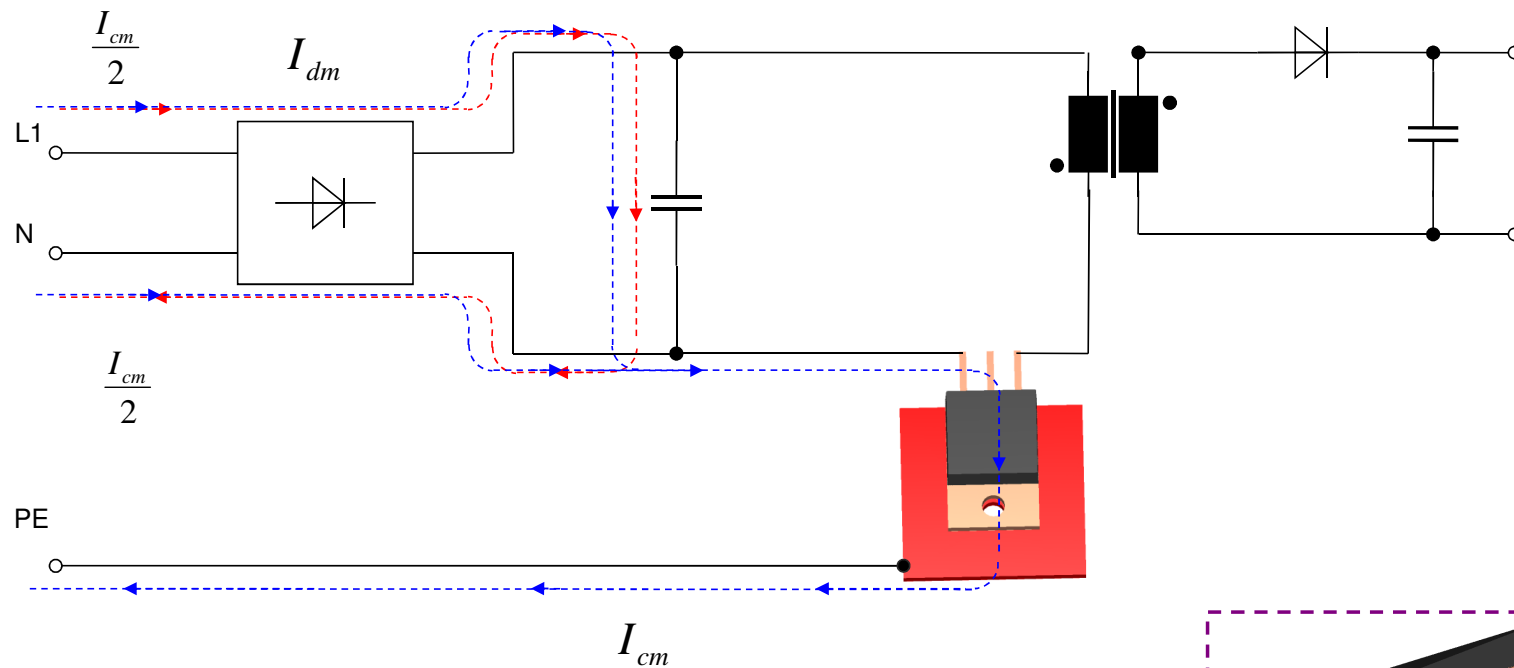


Size	L (mm)	W (mm)	H (mm)
E13/7/4 Vertical	15.0	11.0	16.8
E13/7/4 Horizontal	21.5	15.0	12.0
E16/7/4	18.0	16.5	18.0
E16/8/5	24.5	20.2	16.5



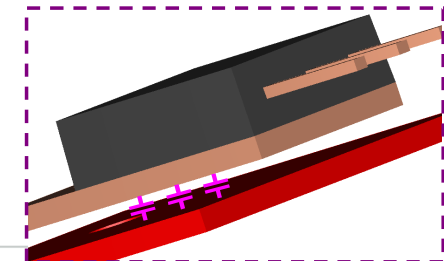
DO NOT FORGET EMC

What noise I'm facing



→ Parasitic capacities

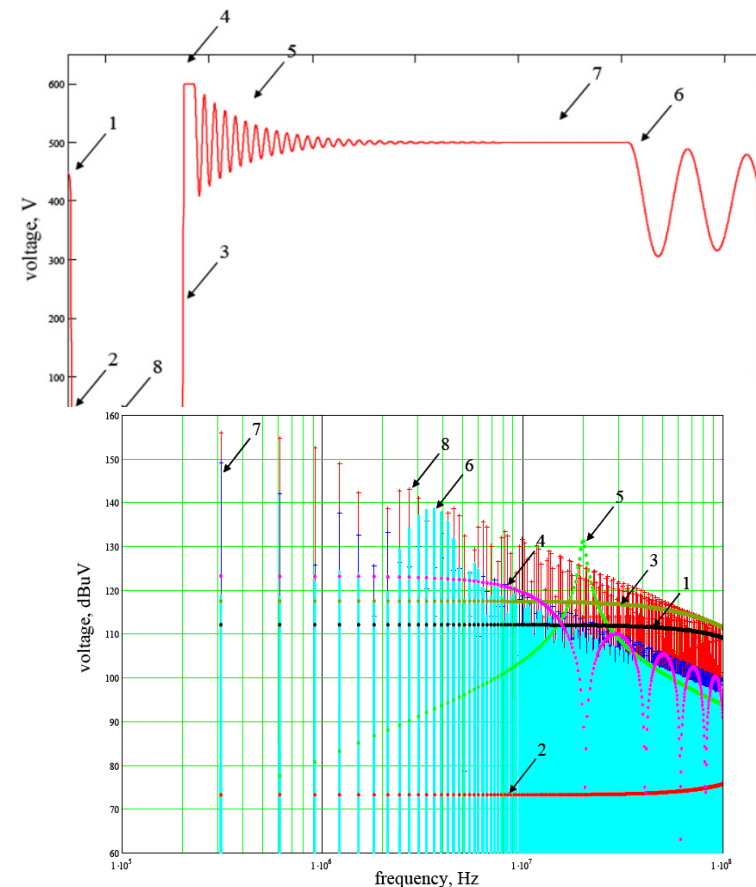
e.g.: collector to cooling element



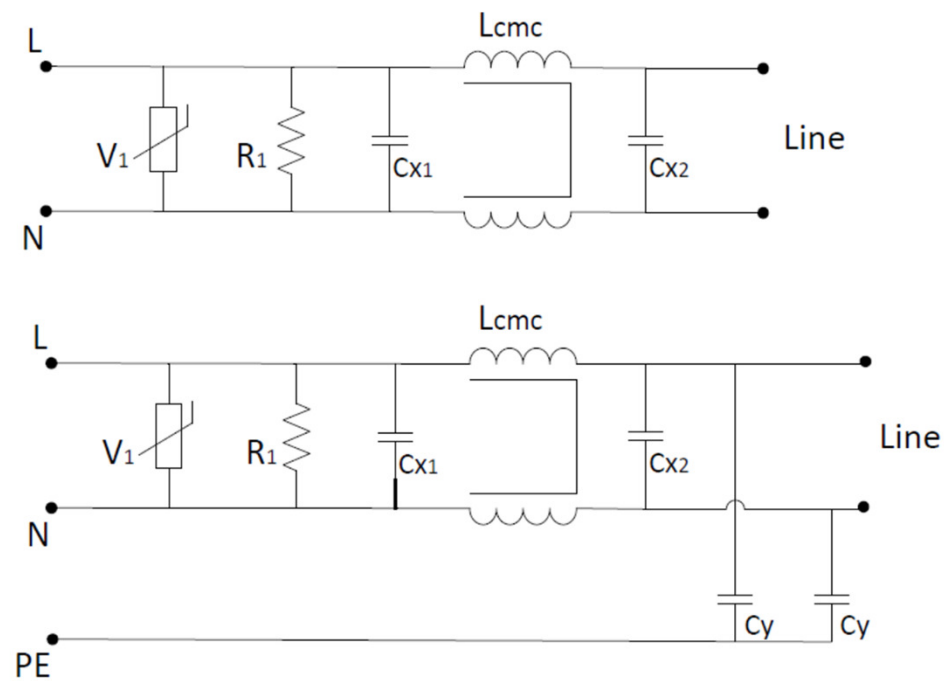
Signal on Vds



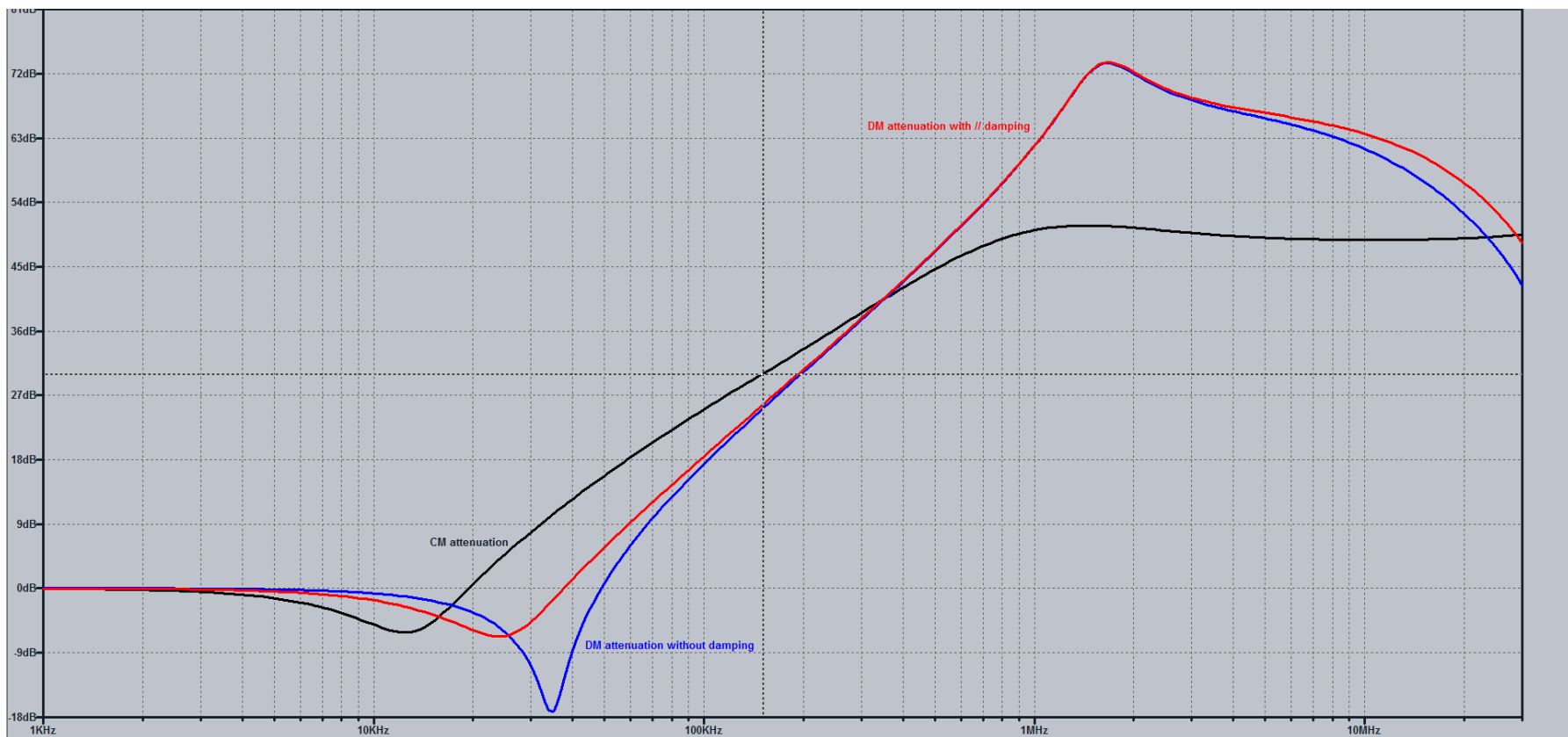
- 1 voltage falls during turn on.
- 2 Parasitic oscillation due to current spike (on time).
- 3 voltages rises during off time.
- 4 Clamping voltage snubber.
- 5 Parasitic oscillation after clamping (due to leakage inductance of transformer and Mosfet capacitance).
- 6 parasitic oscillation after flyback phase (due to Mosfet capacitance and primary inductance of transformer).



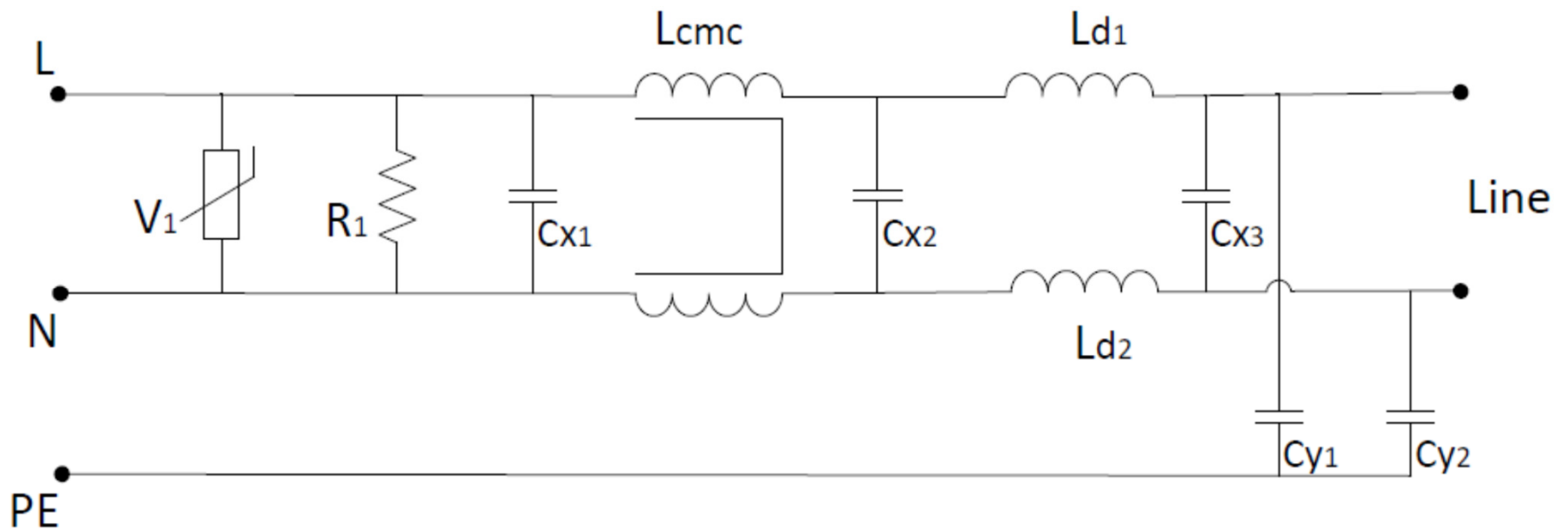
Input filter ideas



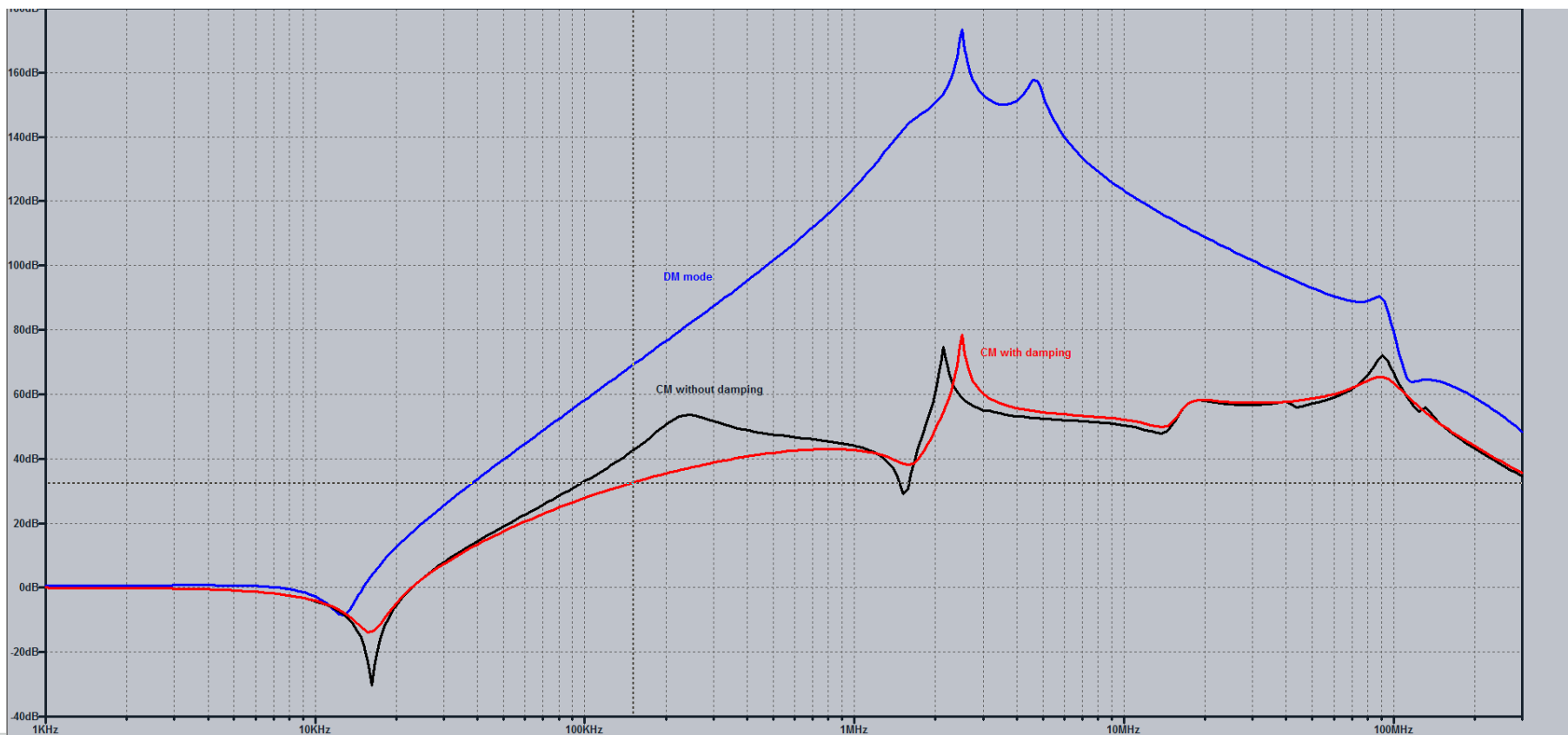
Example of attenuation



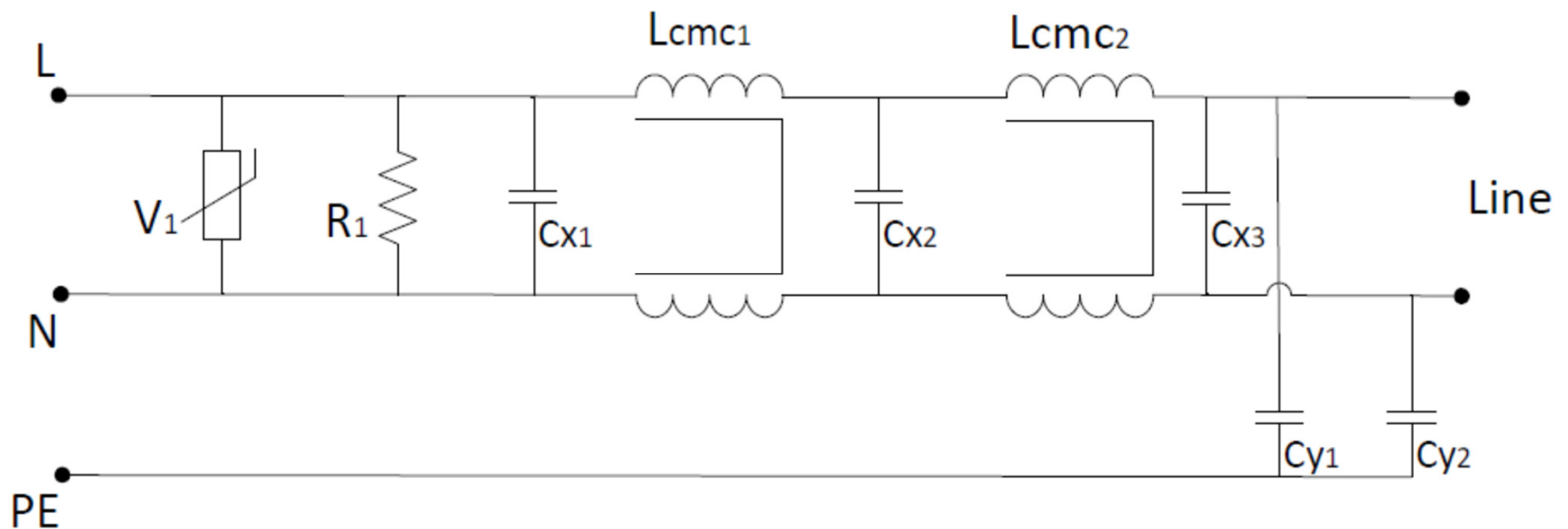
Input filter ideas



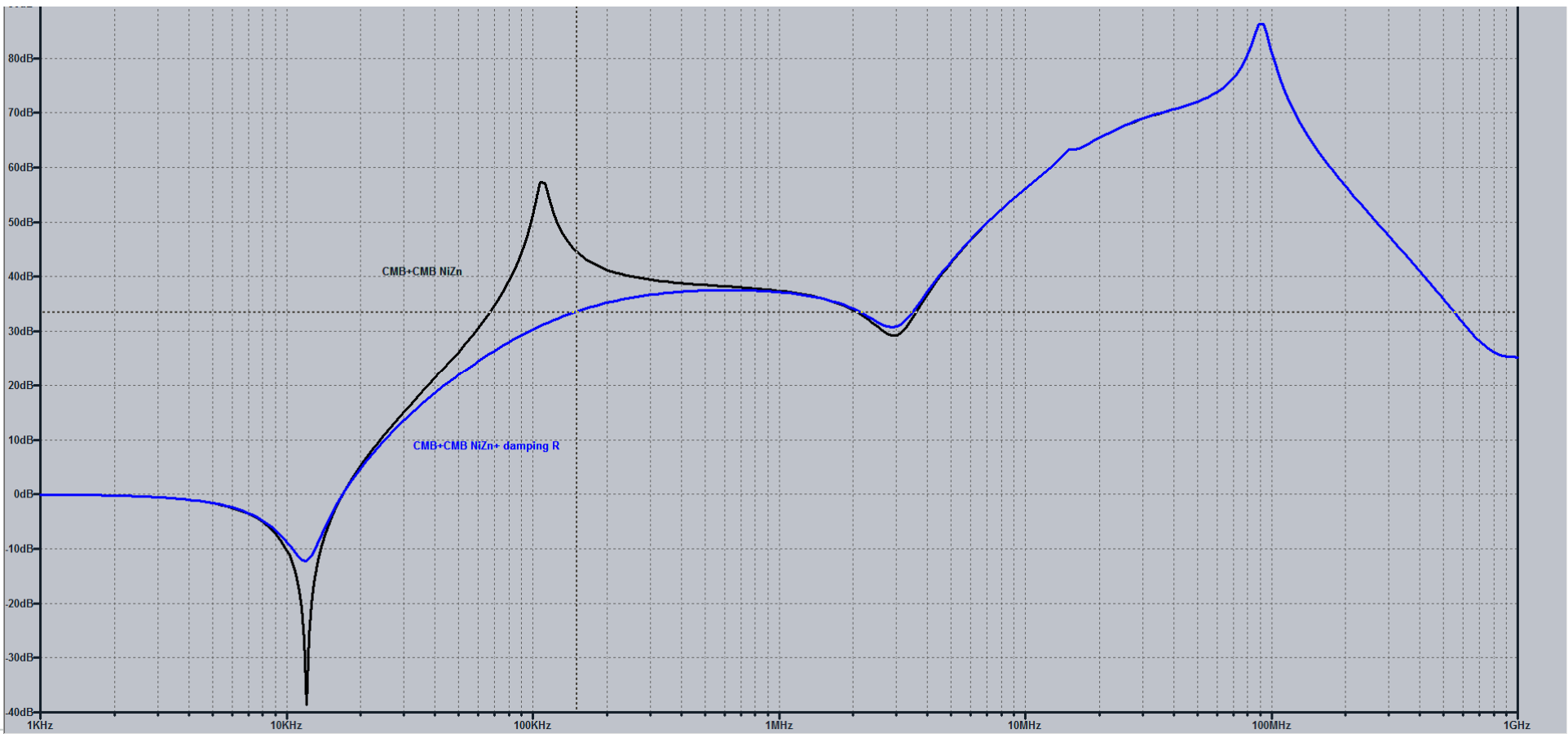
Example of attenuation



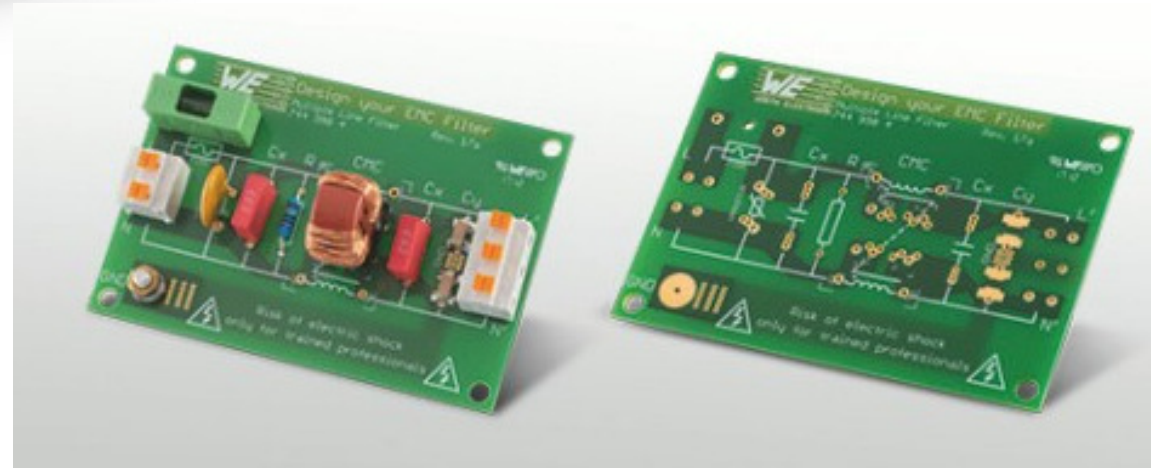
Input filter ideas



CMB+CMB NiZn +R damping



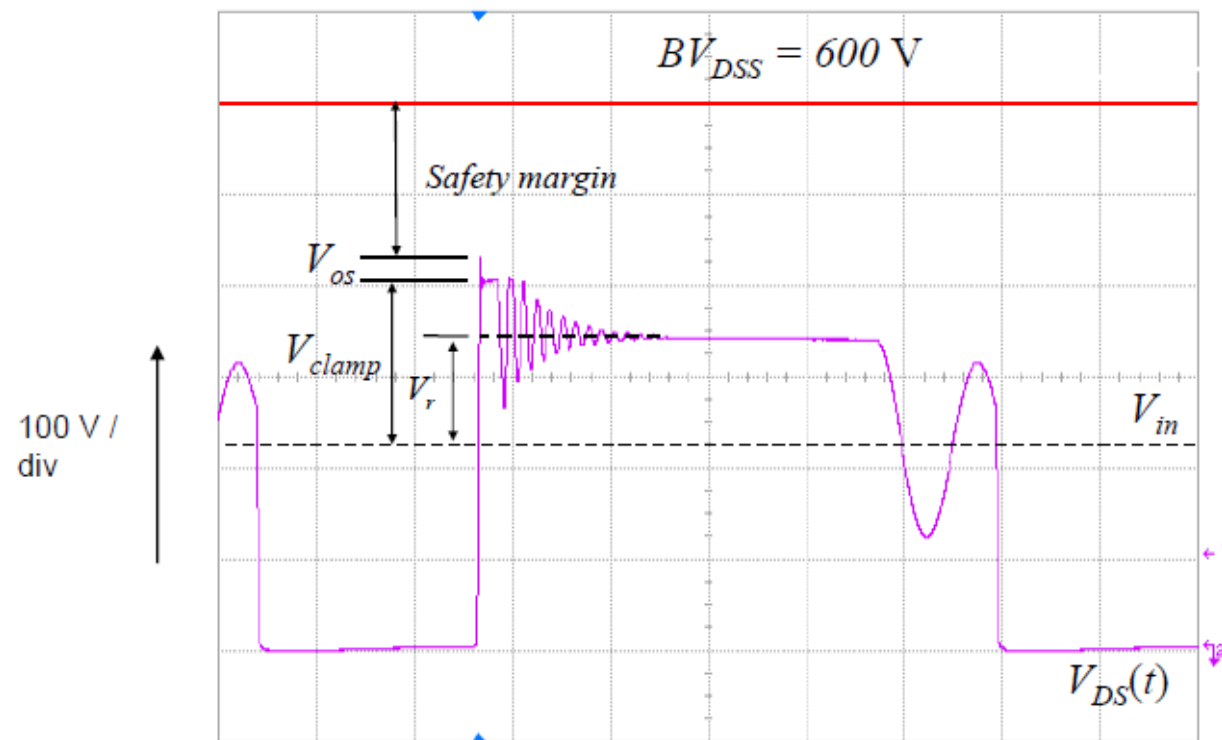
EMC Filter Design Kit **Order Code: 744998**



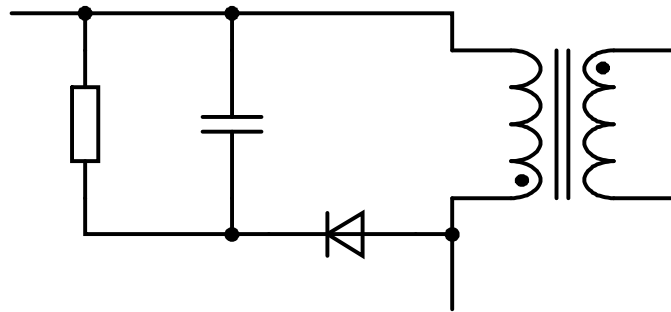


Snubber

Snubber design



Snubber design: First pass selection



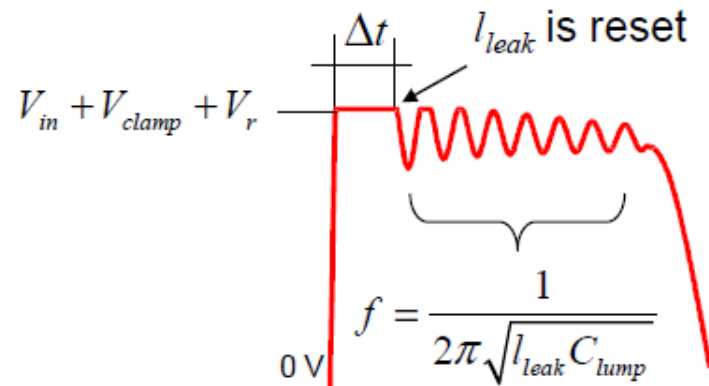
Select desired maximum voltage

$$V_{\text{clamp}} = V_{\text{dss max}} - \text{*safety margin*}$$

$$V_{\text{snub}} = V_{\text{clamp}} - V_{\text{in}}$$

Energy stored into inductor

$$W_1 = \frac{1}{2} \cdot L_l \cdot I_{\text{peak}}^2$$

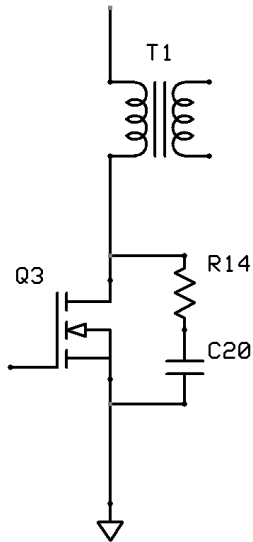


Average power transferred to snubber

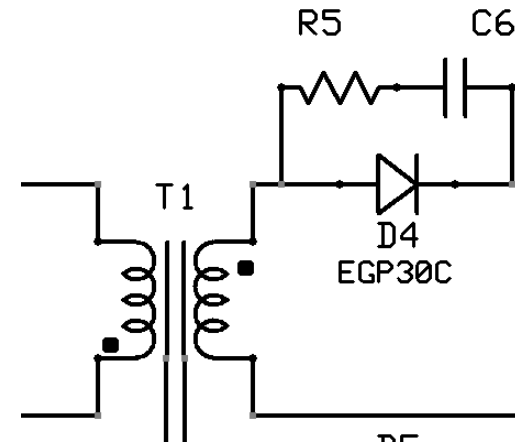
$$P = W_1 \cdot f_{\text{sw}}$$

So choose $R = \frac{V_{\text{snub}}^2}{P}$ and then $RC = \frac{1}{3} T_{\text{on}}$

Diode and Switch Snubbers

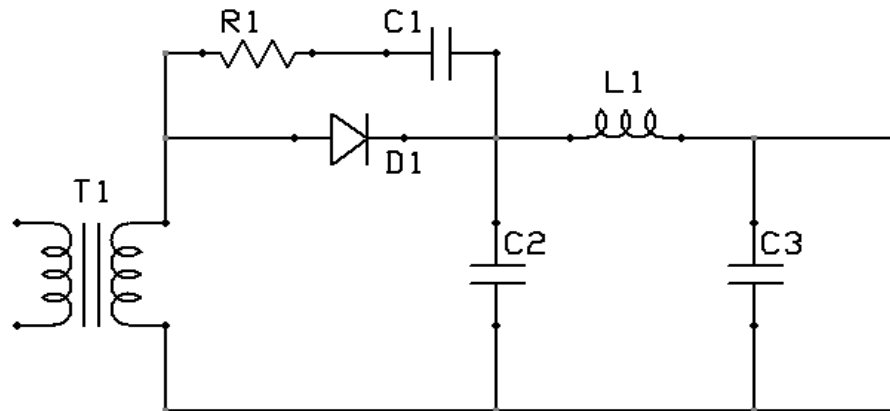


- **Dampens Ringing From**
 - Parasitic PCB Inductance
 - Rectifier Reverse Recovery
 - Output Rectifier Capacitance
- **Capacitor across Diode Reduces Frequency**
- **Resistor to Critically Dampens Ringing**
 - Power Dissipated in Resistor



Output Filter

- Ripple Voltage Determines Capacitance
- ESR Usually Plays a Larger Role
- Often Shown as Single Stage but...
- Two stage can Save Cost by Using Smaller Components
- Second stage often Drum Core Inductor and Ceramic Capacitor



THE END



■ THANK YOU !